

Infrastructure of
Thin Films Laboratory in
Institute of Molecular Physics
Polish Academy of Sciences

Outline

- Sample preparation
 - Magnetron sputtering
 - Ion-beam sputtering
 - Pulsed laser deposition
 - Electron-beam lithography
- Structural characterization
 - SEM – Scanning Electron Microscopy
 - XRR – X-ray Reflectometry
 - XRD – X-ray Diffraction
 - XRF – X-ray Fluorescence
 - Profilometer

Outline

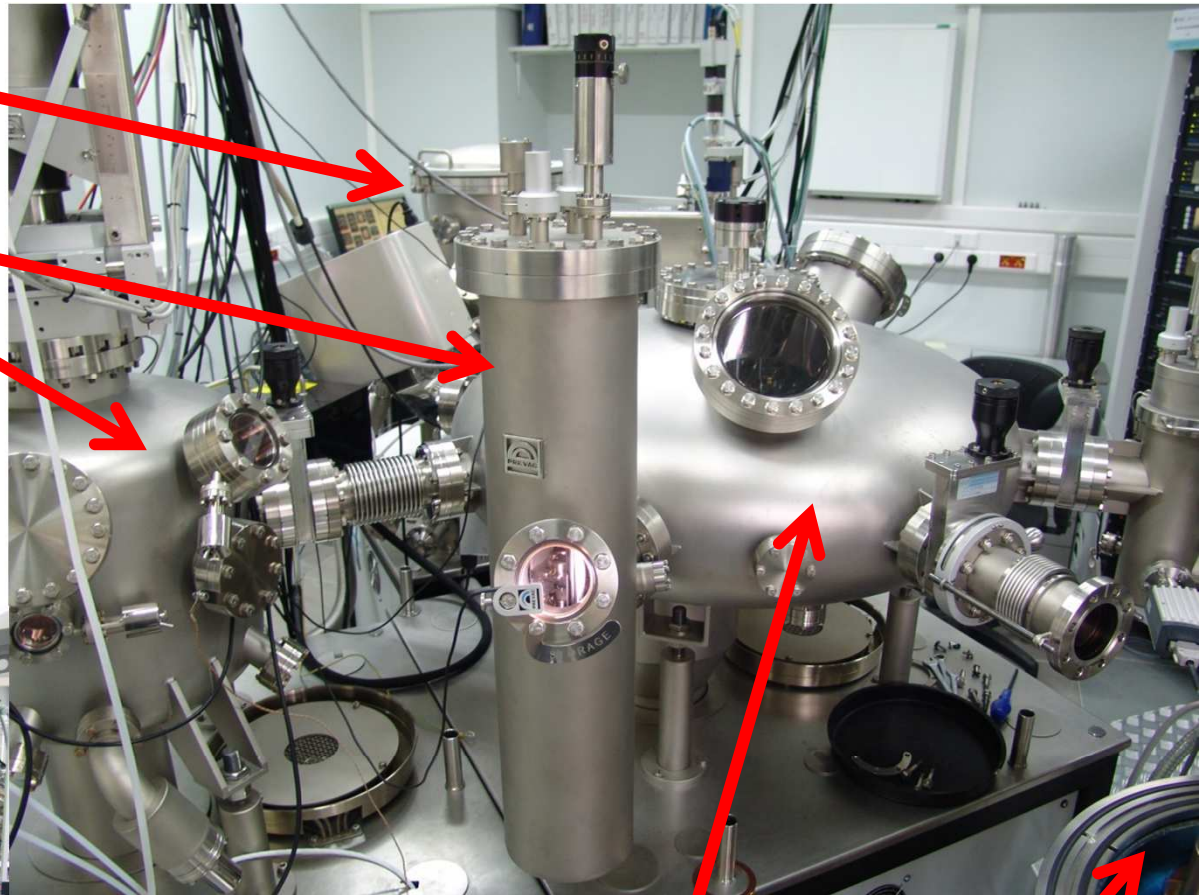
- Static magnetic measurements
 - VSM – Vibrating Sample Magnetometer
 - GMR – Giant Magneto Resistance
 - P-MOKE Magnetometer
 - P-MOKE Microscopy
- Dynamic magnetic measurements
 - VNA-FMR – Vector Network Analyzer – Ferromagnetic Resonance
 - FMR – Ferromagnetic Resonance
 - PIMM – Pulsed inductive microwave magnetometer

UHV system

Ion-beam sputtering

Sample storage

Pulsed laser deposition

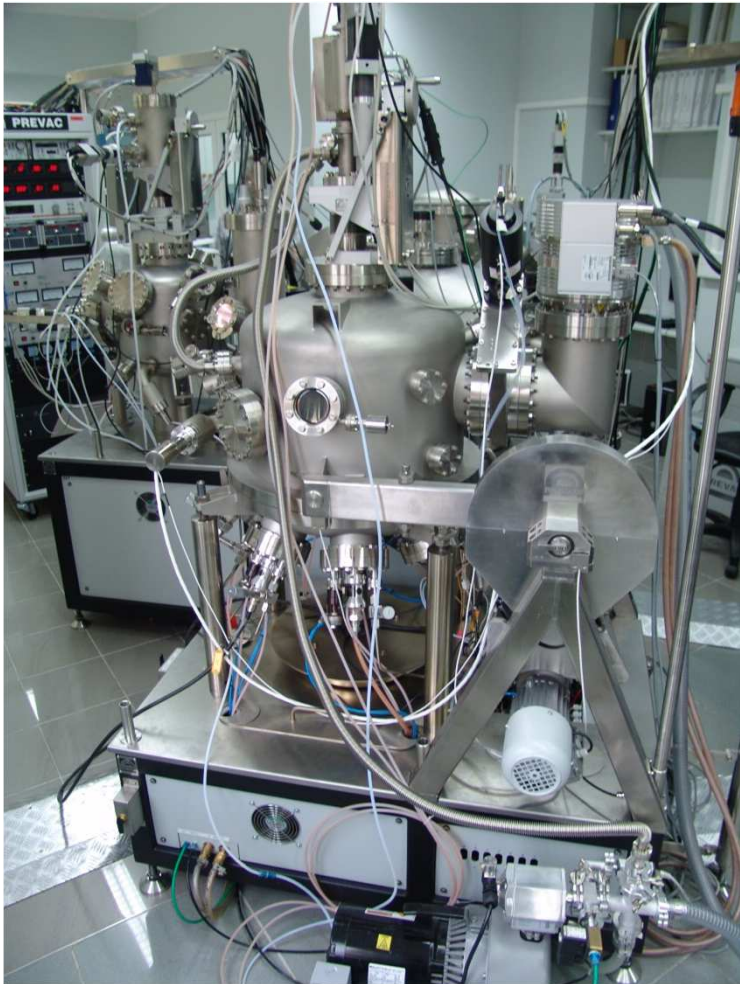


Distribution chamber

Magnetron sputtering



Magnetron sputterings

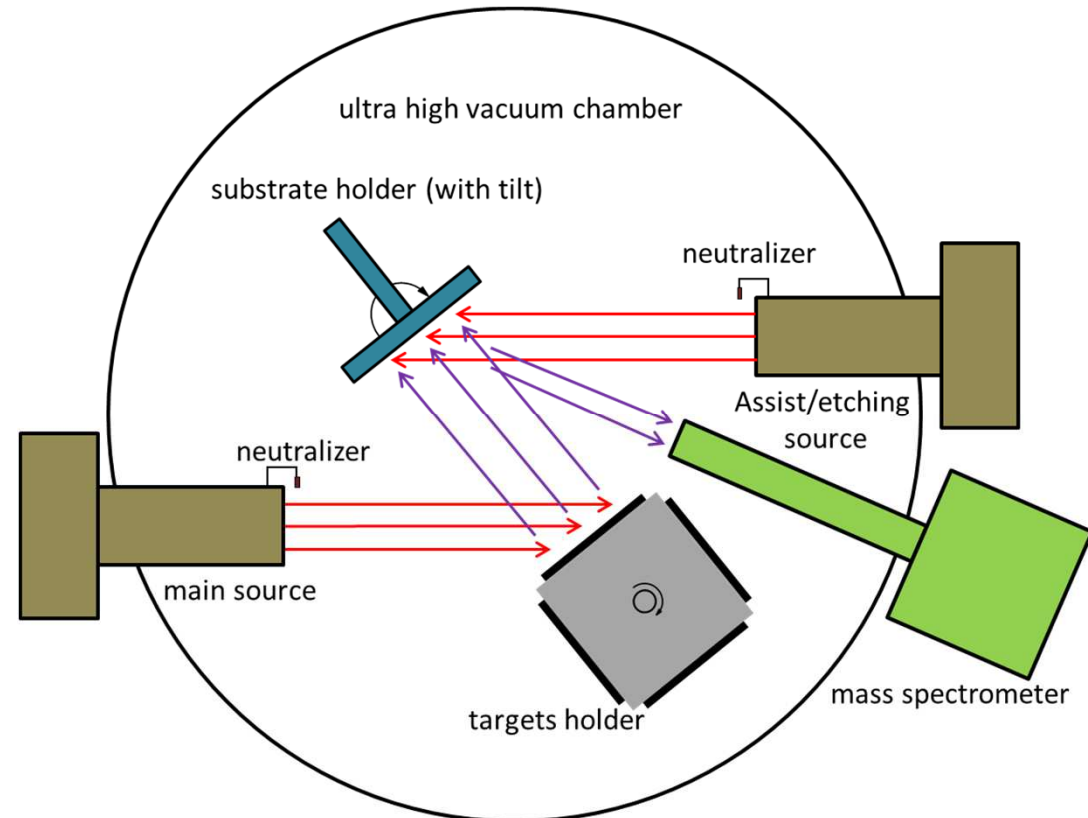
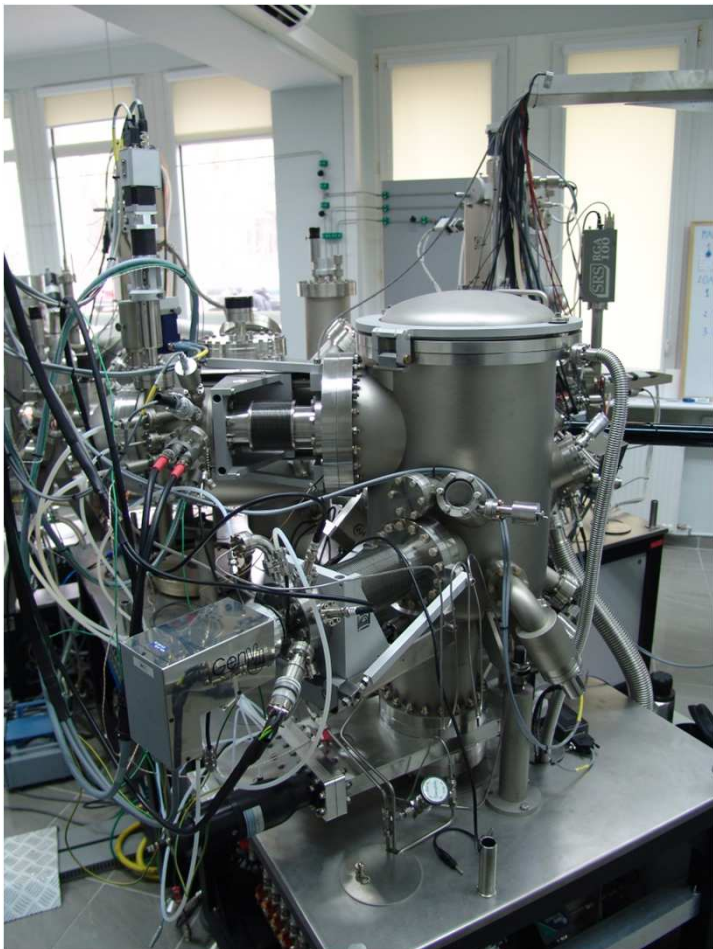


- Base pressure $<5 \times 10^{-9}$ mbar
- Up to 6 ultrapure 2 inch targets
- Possibility to prepare multilayer systems or alloys (confocal setup)
- Possible to make wedge layers
- Sample size - up to 15x20mm

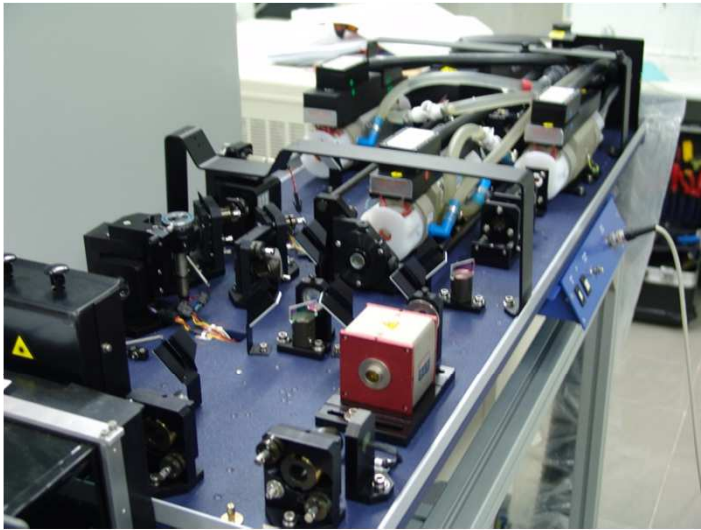


Ion-beam sputtering

- Base pressure $<5 \times 10^{-9}$ mbar
- Up to 4 ultrapure 2 inches targets
- Sample size up to 15x20mm
- Two ion sources – for sputter and etching
- Mass spectrometer



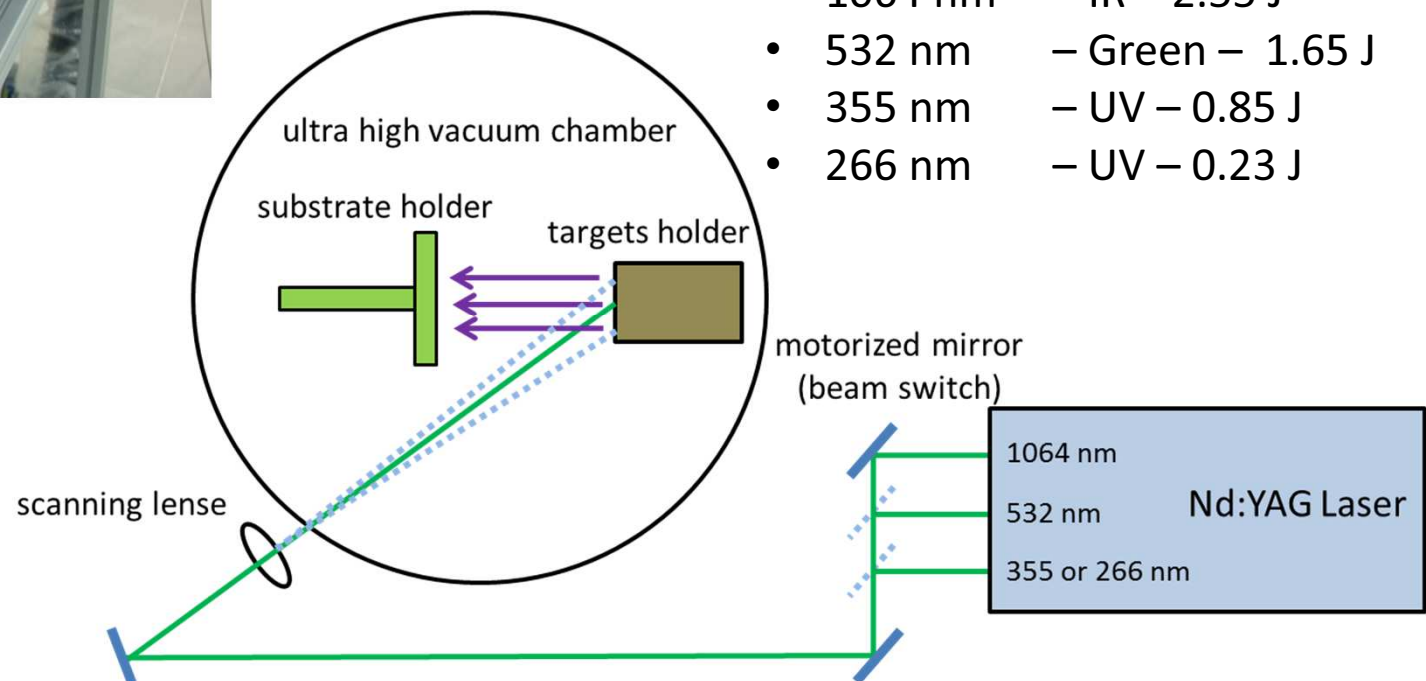
Pulsed laser deposition



- Base pressure $<5 \times 10^{-9}$ mbar
- Up to 6 ultrapure 1 inch targets
- Sample size up to 15x20mm
- Ion source – for etching

Laser:

- 1064 nm – IR – 2.55 J
- 532 nm – Green – 1.65 J
- 355 nm – UV – 0.85 J
- 266 nm – UV – 0.23 J



Electron-beam lithography



- Preparation of samples in CleanRoom class 1000
- PMMA and MMA electron resists in thickness range from $\sim 50\text{nm}$ to a few microns
- Max. wafer size - 150mm (6in.)



SEM



With FEI Nova NanoSEM 650 we can:

- Expand our research capabilities by handling a wider range of sample types
- Perform high resolution imaging - low voltage [1kV] resolution is 1.8nm in low vacuum mode and 1.4 nm in high vacuum mode, so we can still use all the benefits offered by low vacuum imaging without having to sacrifice resolution in images
- Both a high current beam (essential for rapid EDS/EBSD/CL/analytical research) and high resolution at high and low voltage which is essential for image quality across a wide range of sample type are available

Moreover our system includes:

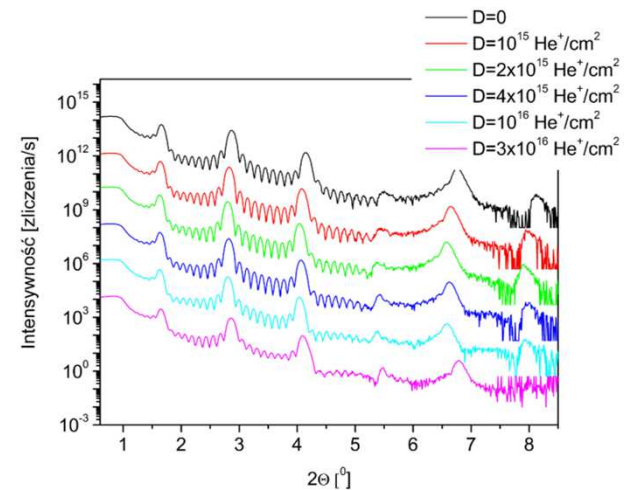
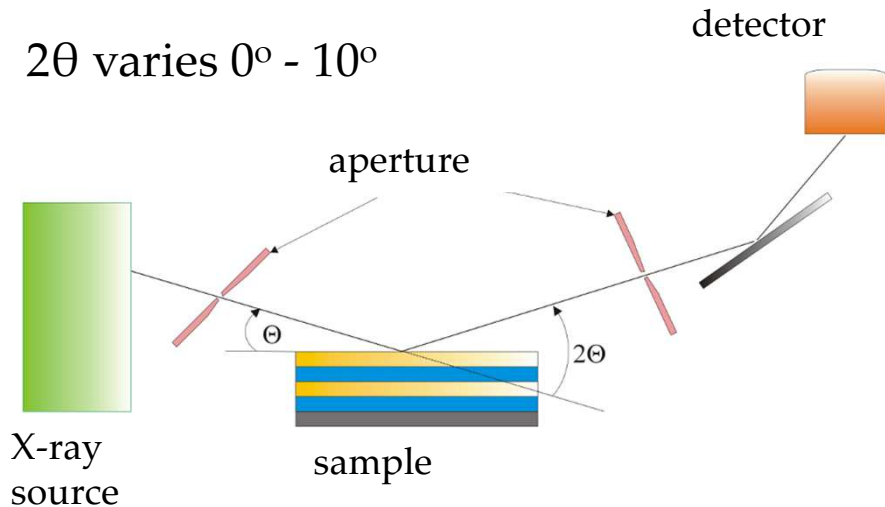
- Bruker EDS system
- Raith lithography system

XRR/XRD

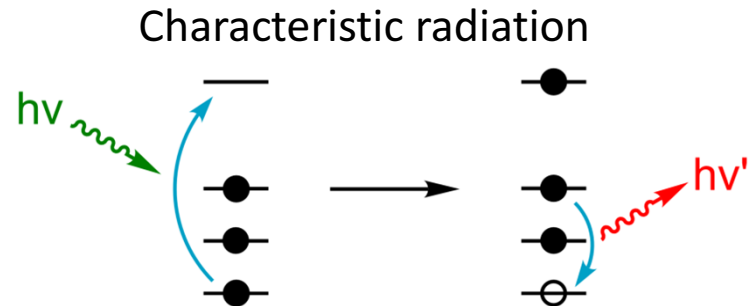
Seifert, model XRD 3003,
X-ray source Cu-K (wavelength
 $\lambda=0.15419$ nm)

Interference of the wave reflected from
surface of the film and the surface of the
substrate results in **Kiessig fringes**.

Allows to measure thickness and
structure of thin films

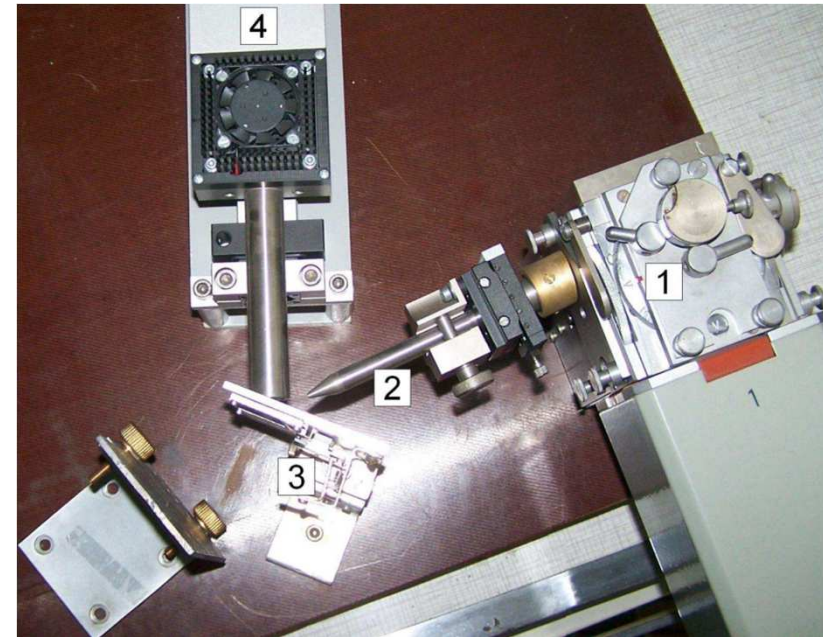


XRF



Multichannel analyzer 10 keV / 1024 channels

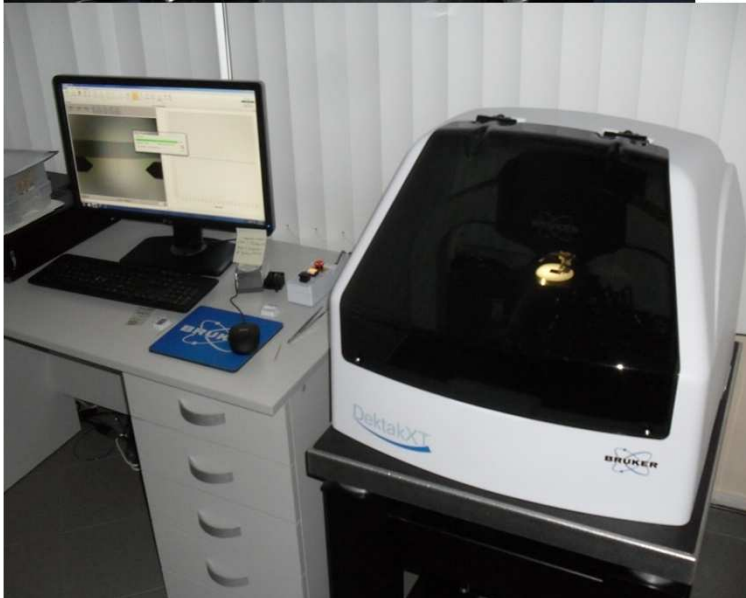
- We can measure:
 - Thickness of thin films (up to 200 nm)
 - Chemical composition



1 – X-ray source, 2 - collimator,
3 – sample holder, 4 - detector

$$t_{\text{sample}} = \frac{I_{\text{sample}}}{I_{\text{reference}}} \cdot t_{\text{reference}}$$

Profilometer

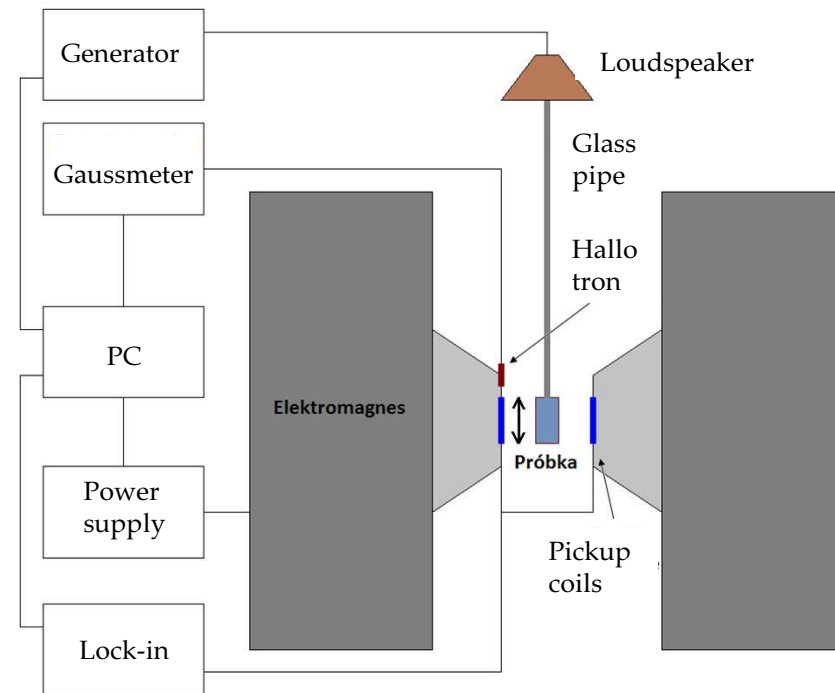


BRUKER – Dektak XT

- Measurement Technique - Stylus profilometry (contact measurement)
- Measurement Capability - Two-dimensional surface profile measurements
- Stylus Force – 0,03 to 15 mg with LIS 3 sensor
- Stylus Options - Stylus radius from 50nm to 25 μ m
- Scan Length Range - 55mm (2 in.)
- Max. Sample Thickness - 50mm (1.95 in.)
- Max. Wafer Size - 200mm (8 in.)
- Step Height Repeatability <math><5 \text{ \AA}</math>, 1 sigma on 0.1 μ m step
- Vertical Resolution – 1 \AA max. (@ 6.55 μ m range)

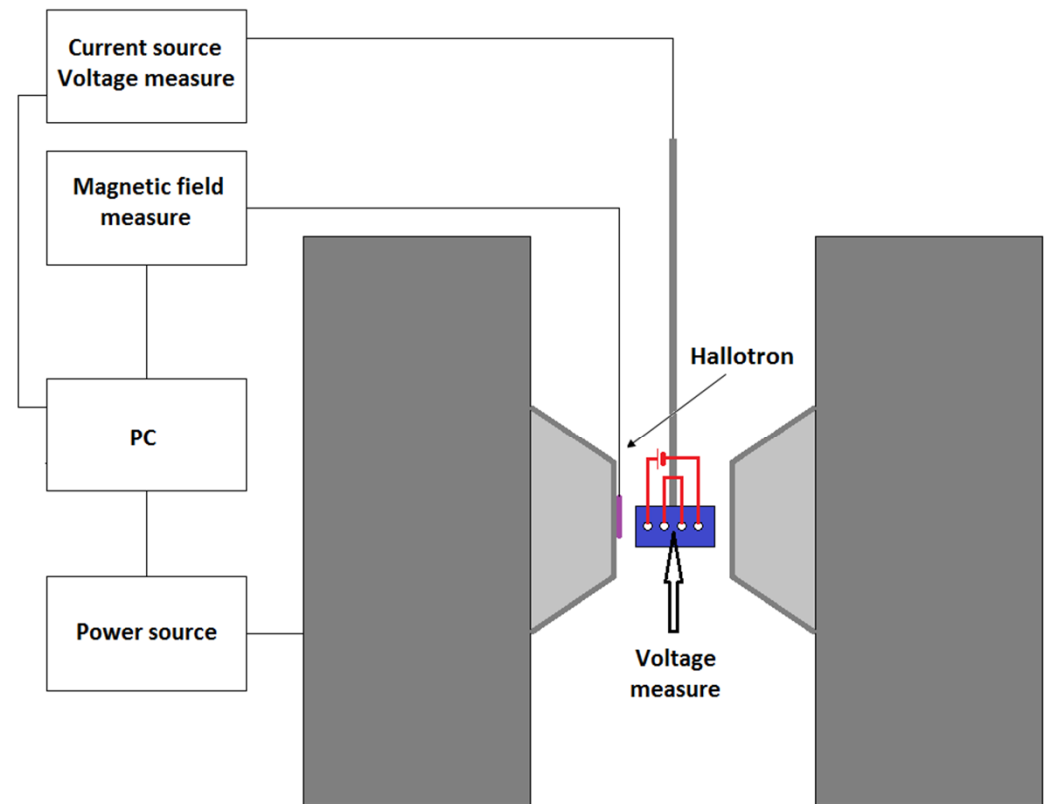
VSM

- Frequency: 35 Hz
- Dual pickup coils
- Magnetic field: up to 16 kOe
- Temperature: -100°C to 250°C

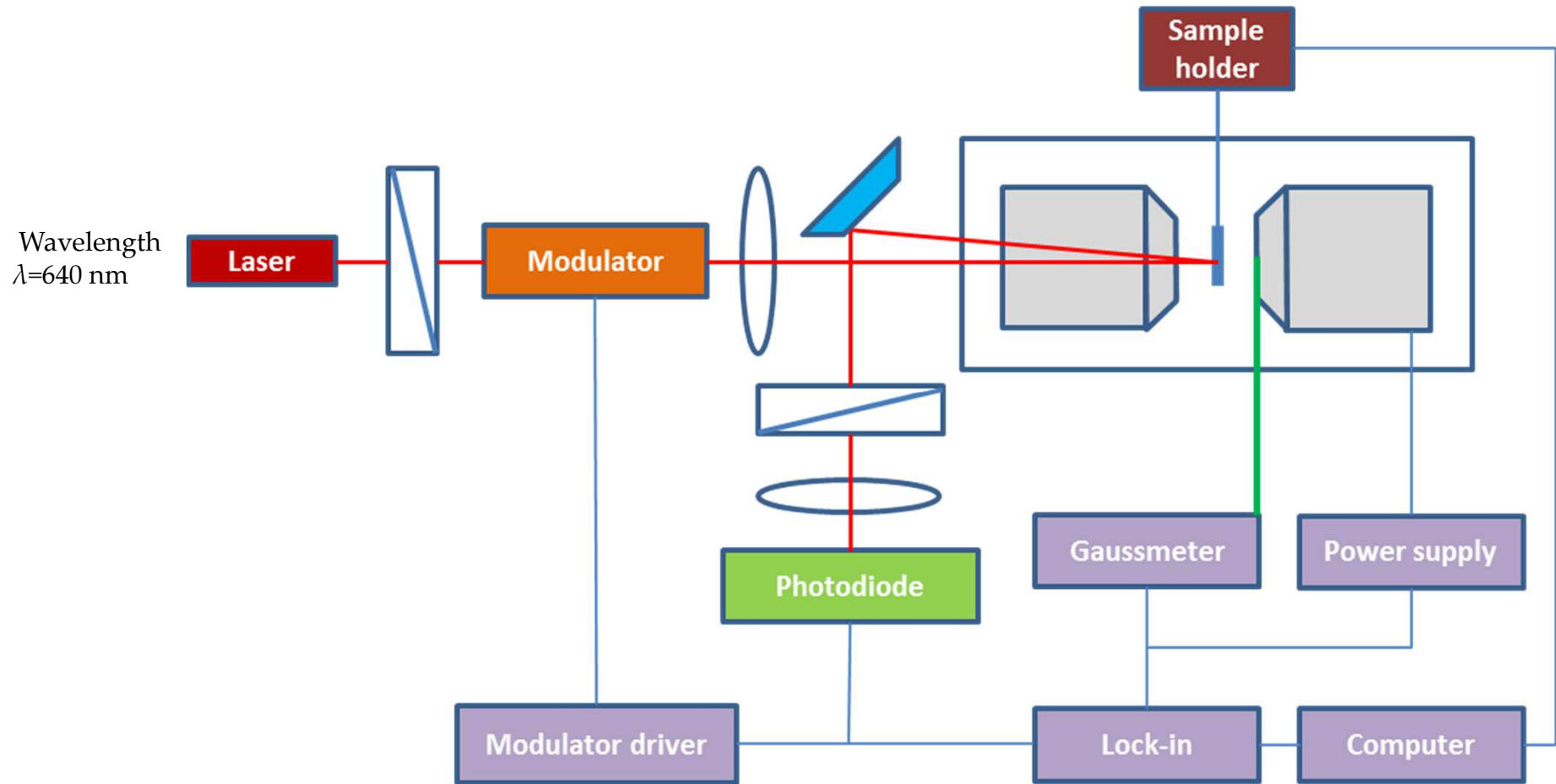


GMR

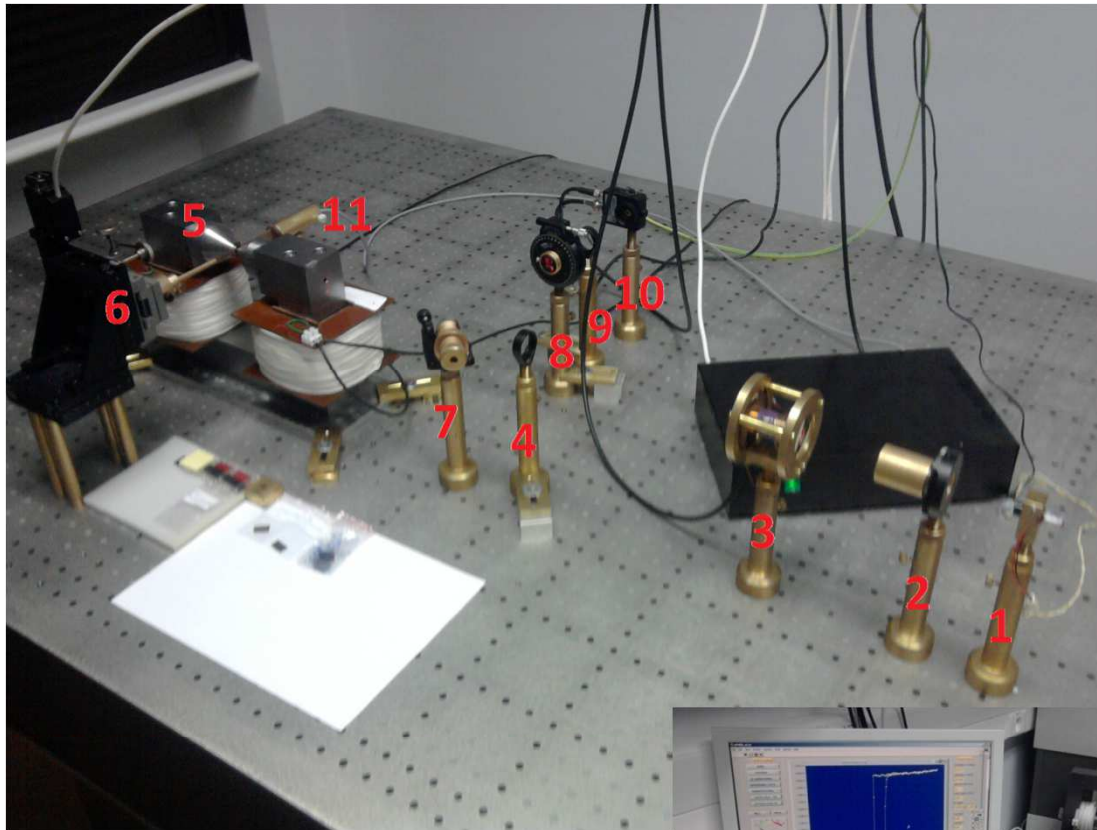
- Four point probe (4 pins) resistivity measurements (2 current / 2 voltage) with magnetic field up to 16 kOe
- Possibility to measure in coils using 11 points (2 current / 9 voltage) with magnetic field up to 0.3 kOe
- Current source 100 nA – 100 μ A



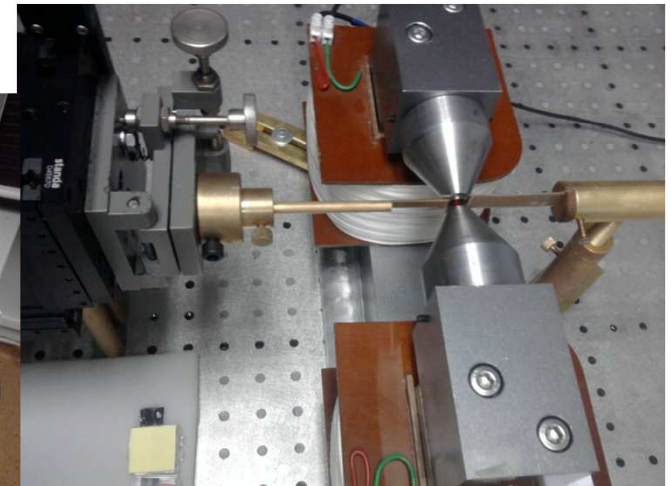
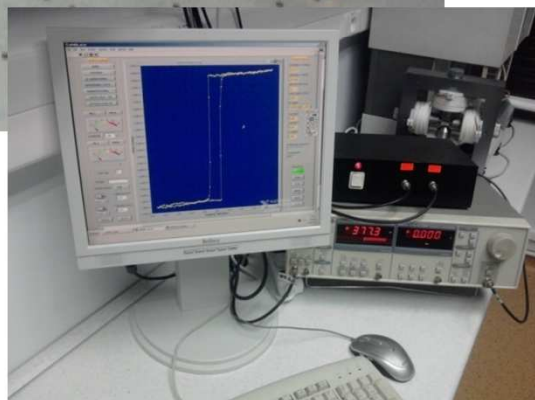
P-MOKE



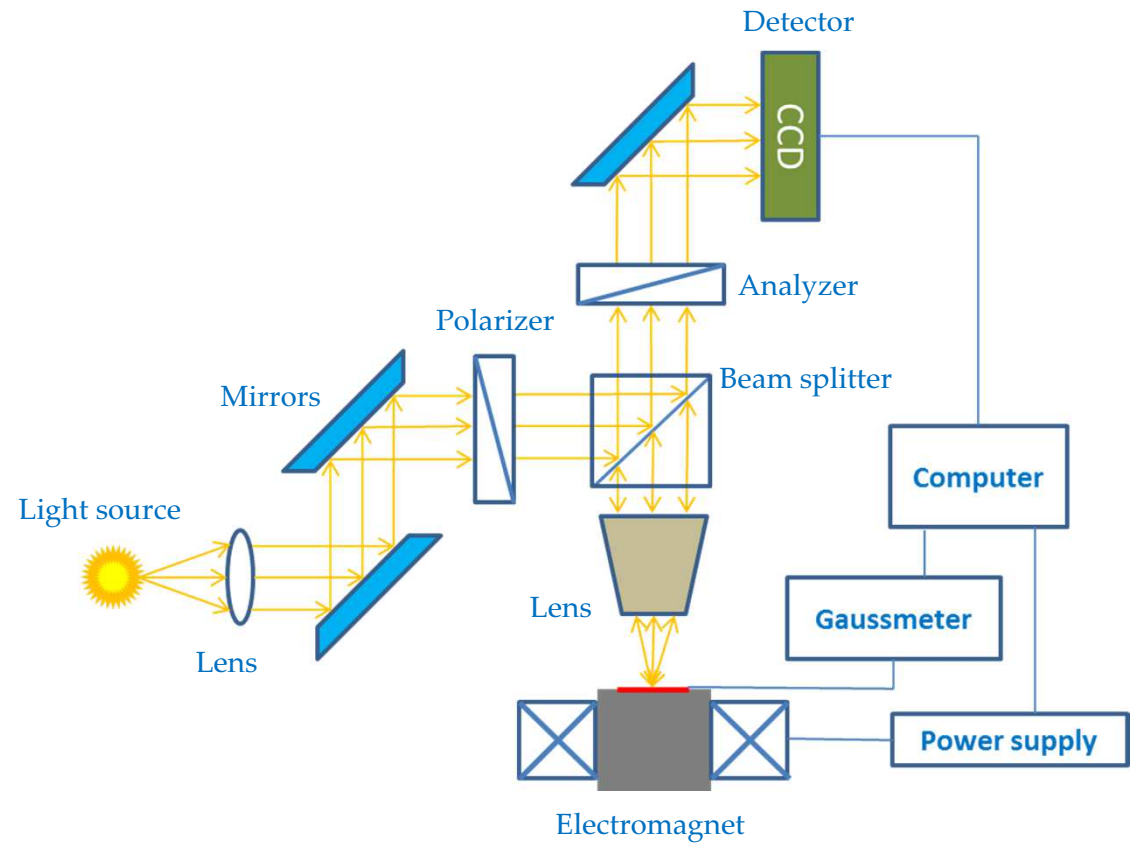
P-MOKE



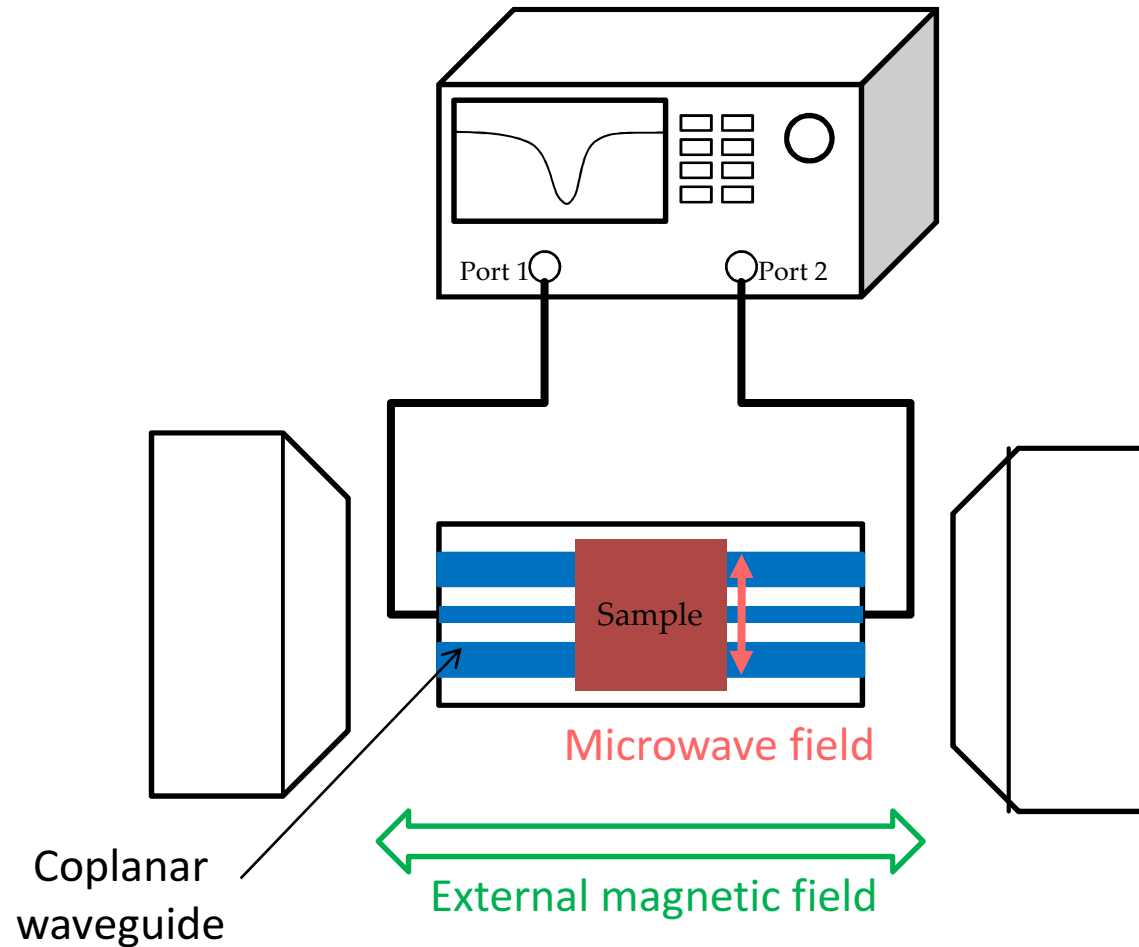
1. Laser diode
2. Polarizer
3. Modulator
4. Lens
5. Electromagnet
6. Sample holder and table
7. Mirror
8. Analyser
9. Lens
10. Detector (fotodiode)
11. Magnetic field sensor



MOKE - Microscopy



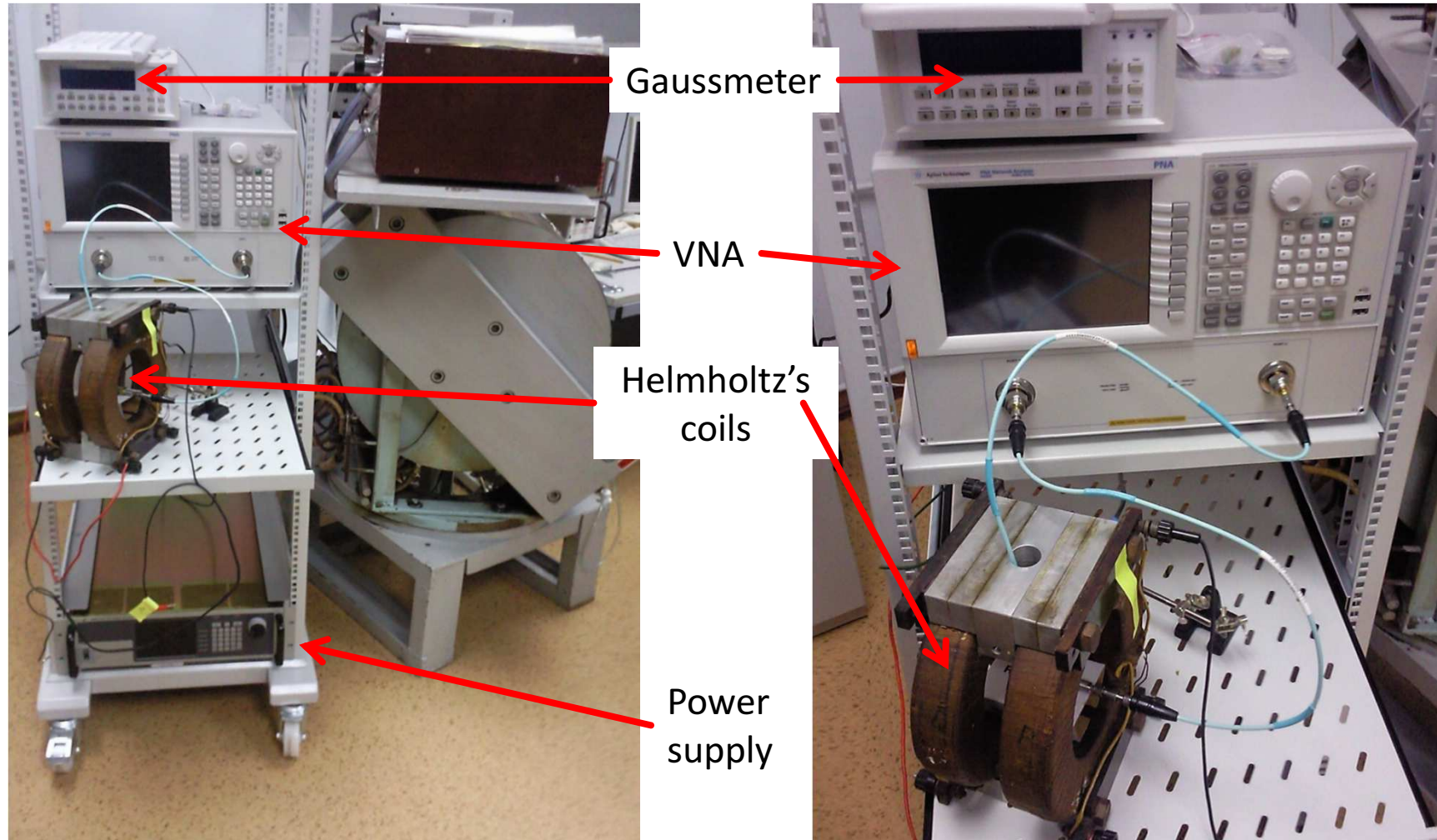
VNA-FMR



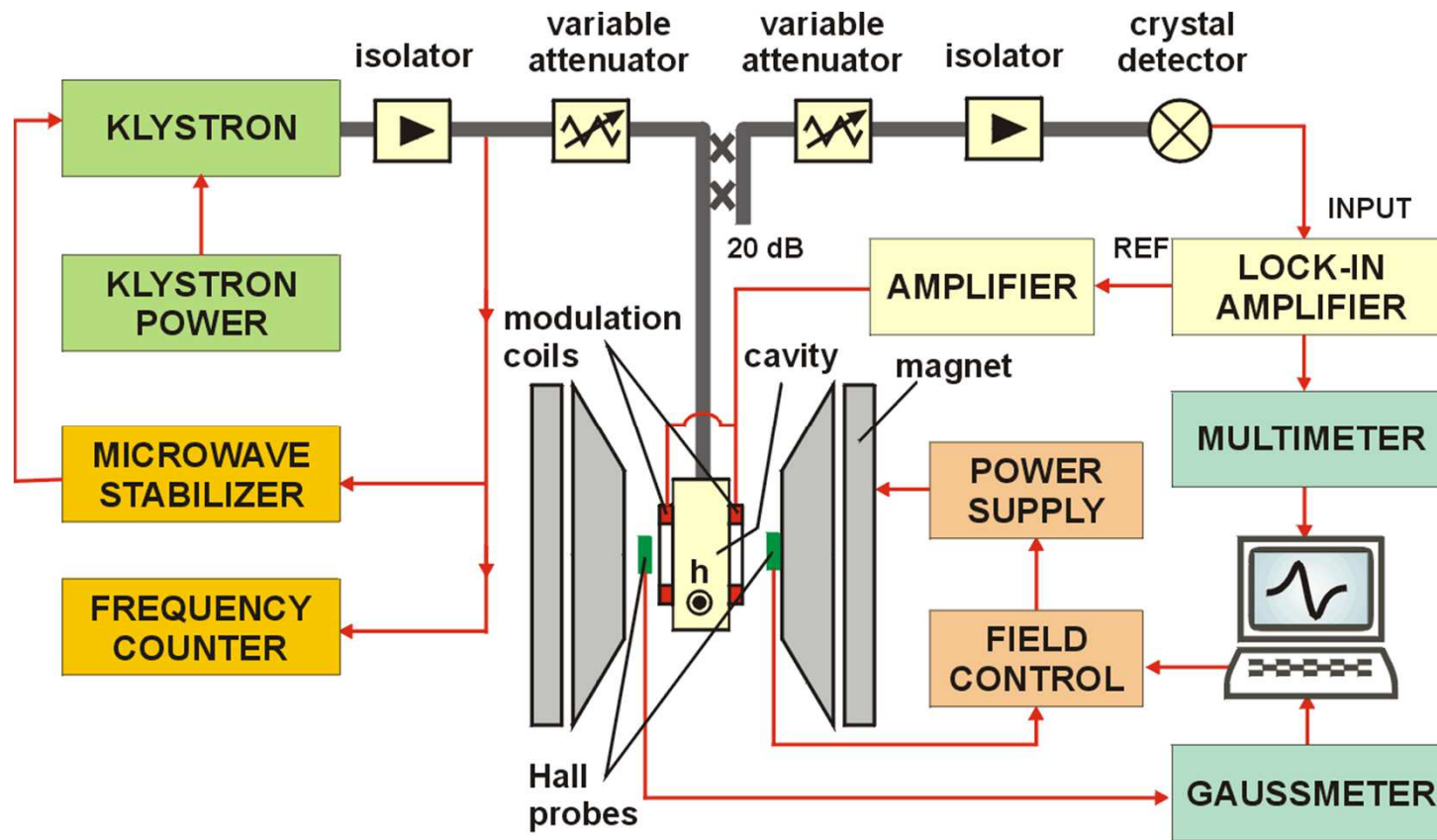
On frequency sweep
FMR experiment
magnetization vector
does not change its
direction

Frequency up to 40 GHz

VNA-FMR

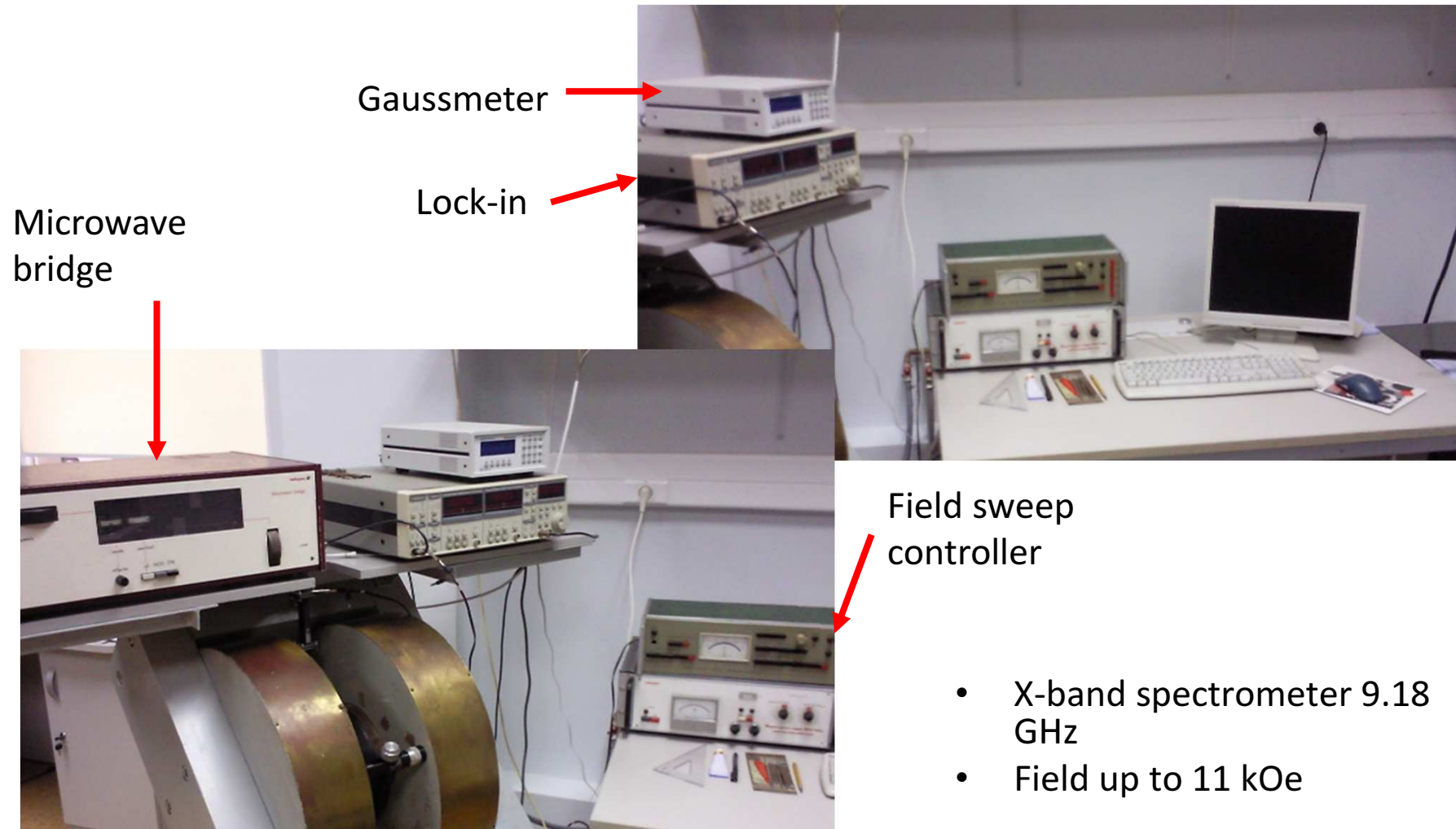


FMR

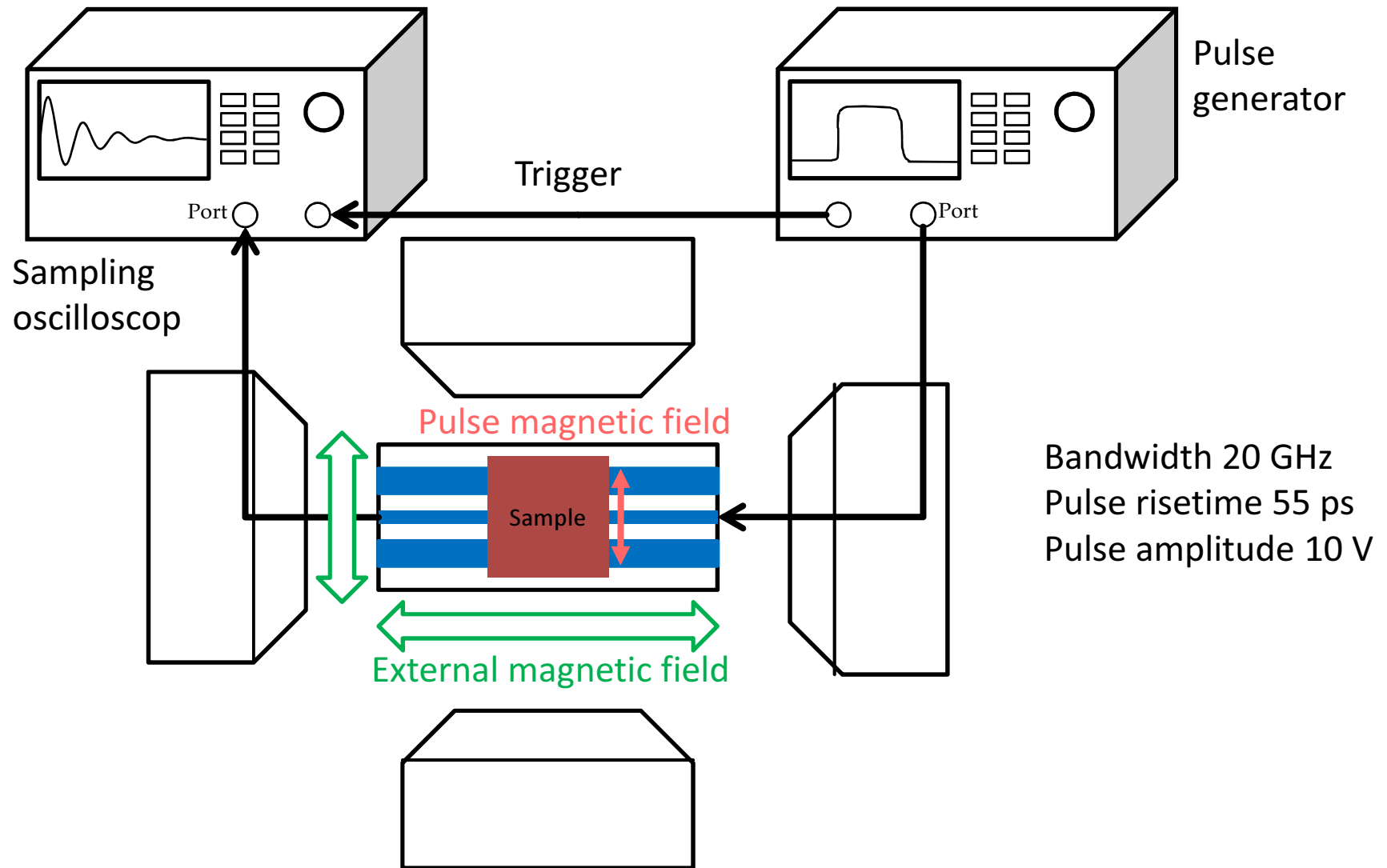


During field sweep FMR experiment magnetization vector changes its direction

FMR



PIMM



PIMM

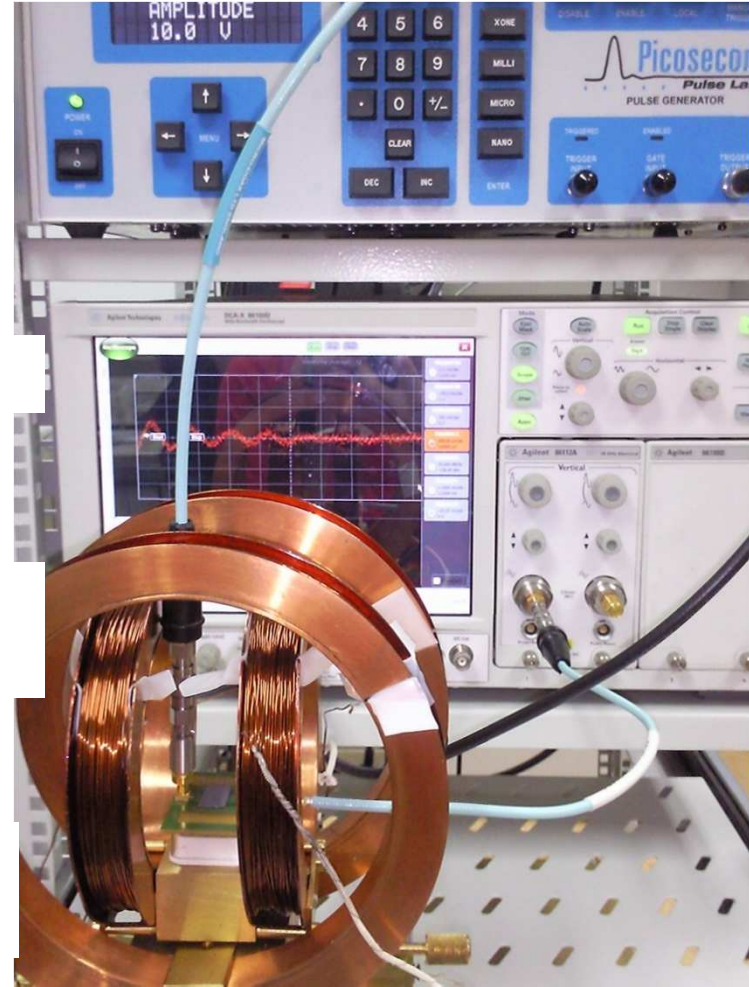


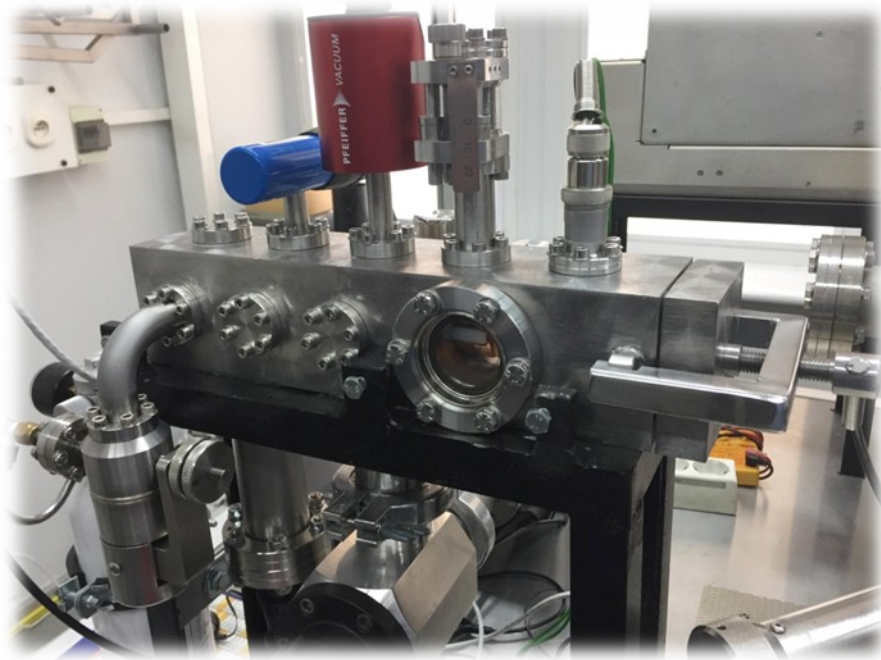
Pulse generator

Oscilloscop

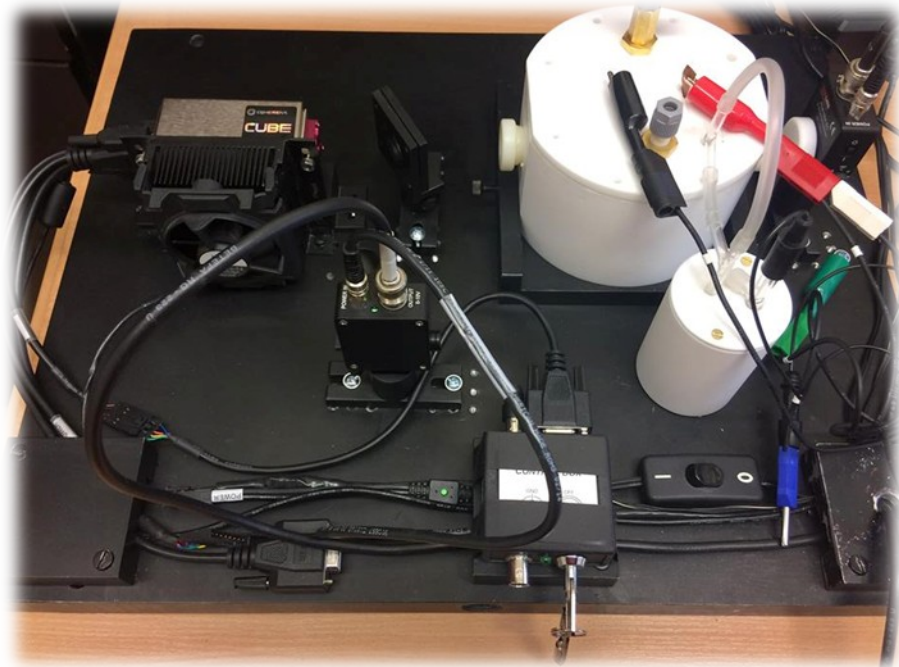
Helmholtz's coils

Power supply





High vacuum equipment for hydrogen (0.01-1000 mbar) absorption/desorption in thin films with optical or electrical monitoring.



Electrochemical equipment for hydrogen absorption/desorption in thin films with optical monitoring.

Plasma Cleaner

- Generator: 40kHz, 0 – 100W
- Gas supply: Mass Flow Controllers (MFCs)
- Vacuum chamber



Oxygene tank



Vacuum pump

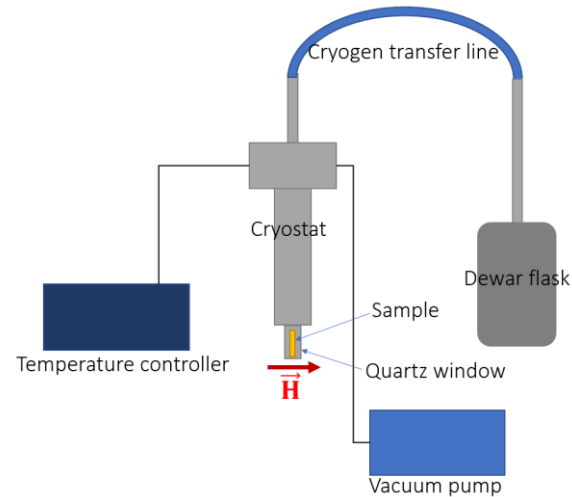


Control panel

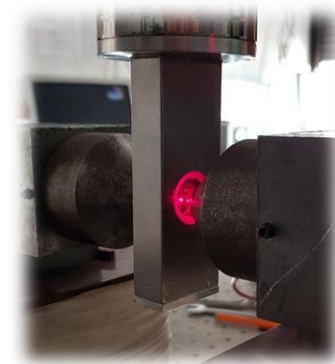
Vacuum chamber with quartz plate

In our research plasma cleaner is using to carried out the process of oxidation of thin films

Cryostat



- Pressure 1×10^{-6} mbar at room temperature
- Temperature range: 4.2K (liquid helium) – 510K
78K (liquid nitrogen) – 510K
- Sample size up to 10x10mm
- Magnetic field range up to 4.5 kOe
- PMOKE measurements



Computer Modelling System



Computing Unit

- 2 CPU x 8-Core, 3GHz, Xeon Gold 5217.
- 512 GB RAM (Samsung)
- 6 GPU x 4352-Cores, 11GB ram, RTX-2080 Ti GPU
- 3x480 GB Samsung SSD

Storage - Postprocessing Unit

- CPU x 8-Core, 3GHz, Xeon Silver 4210
- 32 GB RAM
- 15TB for data storage

Available Software

- Linux Operative System
- GNU, NVCC compilers
- OOMMF (CPU micromagnetism)
- MUMAX (GPU micromagnetism)
- Vampire (Atomistic Simulations)